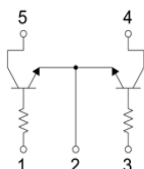


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Two DTC114T (NPN) chips in a package.

EQUIVALENT CIRCUIT



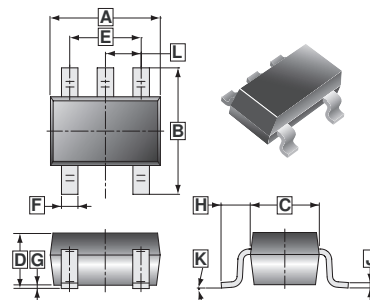
MARKING

G4

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-353	3K	7 inch

SOT-353



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	G	0.100	REF.
B	2.15	2.45	H	0.525	REF.
C	1.15	1.35	J	0.08	0.15
D	0.90	1.10	K	8°	
E	1.20	1.40	L	0.650 TYP.	
F	0.15	0.35			

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	V
Collector-Emitter Voltage	V _{(BR)CEO}	50	V
Emitter-Base Voltage	V _{(BR)EBO}	5	V
Collector Current	I _C	100	mA
Power Dissipation ¹	P _D	150	mW
Junction and Storage Temperature	T _J , T _{STG}	150, -55~150	°C

Notes:

- Each element should not exceed 120mW.

ABSOLUTE MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T_A=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50	-	-	V	I _C =50μA, I _E =0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50	-	-		I _C =1mA, I _B =0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	-	-	V	I _E =50μA, I _C =0
Collector Cut-Off Current	I _{CBO}	-	-	500	nA	V _{CB} =50V, I _E =0
Emitter Cut-Off Current	I _{EBO}	-	-	500	nA	V _{EB} =4V, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-	0.3	V	I _C =10mA, I _B =1mA
DC Current Transfer Ration	h _{FE}	100	250	600		V _{CE} =5V, I _C =1mA
Input Resistance	R ₁	7	10	13	KΩ	
Transition Frequency	f _T	-	250	-	MHz	V _{CE} =10V, I _E =-5mA, f=100MHz

CHARACTERISTICS CURVE

Static Characteristic

